n-channel JFETs *designed for . . .*

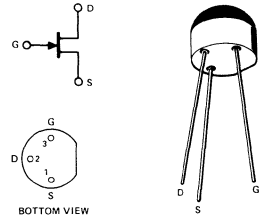
■ General Purpose Switching

Performance Curves NP
See Section 4

BENEFITS

- Very Low Leakage

TO-106
See Section 5



ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Drain or Gate-Source Voltage (Note 1)	−25 V
Gate Current	50 mA
Total Device Dissipation (25°C Free-Air Temperature)	350 mW
Power Derating (to +125°C)	3.5 mW/°C
Storage Temperature Range	−55 to +125°C
Operating Temperature Range	−55 to +125°C
Lead Temperature (1/16" from case for 10 seconds)	300°C

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

		Characteristic		E204 Min	E204 Typ	E204 Max	Unit	Test Conditions	
1	STATIC	I_{GSS}	Gate Reverse Current (Note 2)			−100	pA	V_{DS} = 0, V_{GS} = −20 V	
2	STATIC	$V_{GS(off)}$	Gate-Source Cutoff Voltage	−0.5		−2.0	V	V_{DS} = 20 V, I_D = 10 nA	
3	STATIC	BV_{GSS}	Gate-Source Breakdown Voltage	−25			V	V_{DS} = 0, I_G = −1 μA	
4	STATIC	I_{DSS}	Saturation Drain Current (Note 3)		1.2		mA	V_{DS} = 20 V, V_{GS} = 0	
5	STATIC	I_G	Gate Current (Note 2)		−35		pA	V_{DG} = 20 V, I_D = 200 μA	
6	DYNAMIC	g_{fs}	Common Source Forward Transconductance (Note 3)		1500		μmho	V_{DS} = 20 V, V_{GS} = 0	f = 1 kHz
7	DYNAMIC	g_{os}	Common-Source Output Conductance		2.5		μmho	V_{DS} = 20 V, V_{GS} = 0	f = 1 kHz
8	DYNAMIC	C_{iss}	Common-Source Input Capacitance		5		pF	V_{DS} = 20 V, V_{GS} = 0	f = 1 MHz
9	DYNAMIC	C_{rss}	Common-Source Reverse Transfer Capacitance		2		pF	V_{DS} = 20 V, V_{GS} = 0	f = 1 MHz
10	DYNAMIC	$\bar{e}_n$	Equivalent Short-Circuit Input Noise Voltage		10		$\frac{nV}{\sqrt{Hz}}$	V_{DS} = 10 V, V_{GS} = 0	f = 1 kHz

NOTES:

NP

1. Geometry is symmetrical. Units may be operated with source and drain leads interchanged.
2. Approximately doubles for every 10°C increase in T_A.
3. Pulse test duration = 2 ms.